

FORM PTO-1449 (SUBSTITUTE)

Attorney Docket No.:

Applic. No.

Z&amp;PINFN10277

10/027,533

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE  
STATEMENT BY APPLICANT  
(37 CFR 1.98(b))

Applicant

Walter Hartner et al.

Filing Date

Group Art Unit

December 26, 2001

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
BT	A	5,130,172	07/14/92	Hicks et al.			
	B	5,296,255	03/22/94	Gland et al.			
	C	5,320,978	06/14/94	Hsu			
	D	5,403,620	04/04/95	Kaesz et al.			
	E	5,440,173	08/08/95	Evans, Jr. et al.			
	F	5,789,320	08/04/98	Andricacos et al.			
	G	5,807,788	09/15/98	Brodsky et al.			
BT	H	5,824,563	10/20/98	Hwang			
	I						

## FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES	NO
BT	J	198 48 444 A1	12/23/99	Germany				X
BT	K	0 567 878 A1	11/03/93	Europe			X	
	L							
	M							
	N							

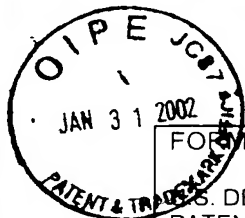
## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

BT	O	Ziling Xue et al.: "Organometallic Chemical Vapor Deposition of Platinum Reaction Kinetics and Vapor Pressures of Precursors", Chem. Mater. 1992, No. 4, pp. 162-166
BT	P	Ju-Hong Kwon et al.: "Preparation of Pt thin films deposited by metalorganic chemical vapor deposition for ferroelectric thin films", Thin Solid Films, Vol. 3, 1997, pp. 136-142

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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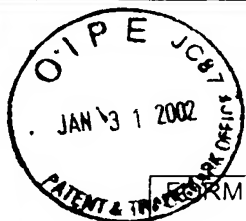
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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J						
	K						
	L						
	M						
	N						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

BT	O	Tomonori Aoyama et al.: "Chemical Vapor Deposition of Ru and Its Application in (Ba, Sr)TiO <sub>3</sub> Capacitors for Future DRAM", International Conference on Solid State Devices and Materials, Japan Society of Applied Physics, Tokyo, September 1998, pp. 44-45
BT	P	B.S. Kwak et al.: "Study of epitaxial platinum thin films grown by metalorganic chemical vapor deposition", Journal of Applied Physics, October 15, 1992, Vol. 72, No. 8, pp. 3735-3740

EXAMINER B. Talbot	DATE CONSIDERED 6/2/03
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	K						
	L						
	M						
	N						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

BT	O	Alfred A. Zinn et al.: "Metal CVD", chapter 7, "Chemical Vapor Deposition of Platinum, Palladium and Nickel", VCH-Weinheim, 1994, pp. 329-355
	P	

EXAMINER B. Talbot	DATE CONSIDERED 6/2/03
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